

**SGS-THOMSON**

MICROELECTRONICS

TLC 111 B → TLC 381 B**S G S-THOMSON****TRIACS**

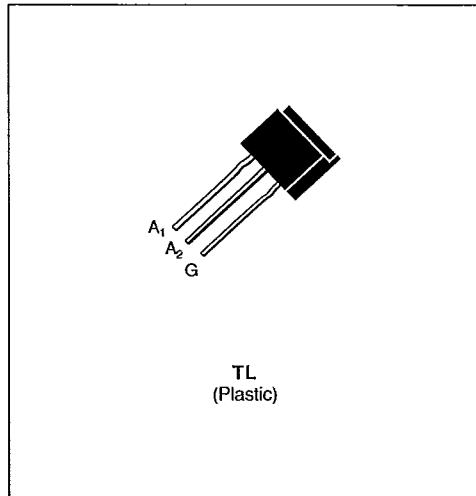
- GLASS PASSIVATED CHIP
- HIGH SURGE CURRENT

DESCRIPTION

Low power triacs suited for 50 and 60 Hz up to 380 V_{RMS}.

APPLICATIONS

- CONTROL SPEED FOR LITTLE MOTORS ; ELECTRIC PUMP OR VENTILATOR, SEWING MACHINE
- RELAY, DETECTOR, ALARM SYSTEM
- ELECTRONIC STARTER FOR LAMP
- HIGH POWER TRIAC DRIVER

**ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state Current (360° conduction angle)	1	A
I _{T(RMS)}	RMS on-state Current on Printed Circuit (360° conduction angle)	0.77	A
I _{TSM}	t = 8.3 ms	16	A
	t = 10 ms	15	
I ² t	I ² t Value for Fusing	1.125	A ² s
dI/dt	Critical Rate of Rise of on-state Current (1)	10	A/μs
T _{stg} T _j	Storage and Operating Junction Temperature Range	-40 to 150 -40 to 110	°C °C

Symbol	Parameter	TLC111B	TLC221B	TLC331B	TLC381B	Unit
V _{DORM}	Repetitive Peak off-state Voltage (2)	200	400	600	700	V

(1) I_G = 500 mA dI_G/dt = 1 A/μs(2) T_j = 110 °C.**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to Ambient on Printed Circuit	75	°C/W
R _{th(j-L)}	Junction-leads for 360° Conduction Angle (F = 50 Hz)	45	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{GM} = 2 \text{ W}$ ($t_p = 10 \mu\text{s}$) $I_{GM} = 1 \text{ A}$ ($t_p = 10 \mu\text{s}$)
 $P_{G(AV)} = 0.1 \text{ W}$ $V_{GM} = 16 \text{ V}$ ($t_p = 10 \mu\text{s}$)

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T-25-13

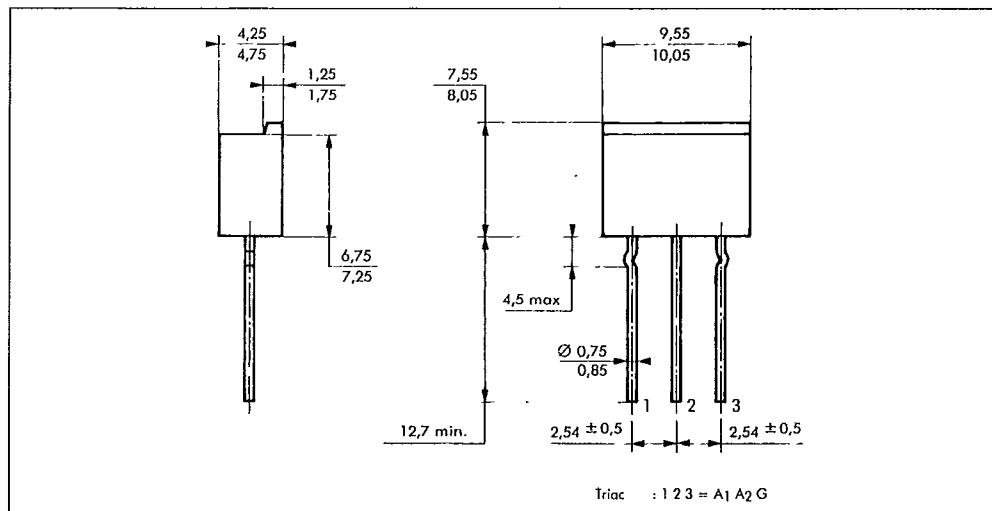
ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	$T_J = 25^\circ\text{C}$ $V_D = 12 \text{ V}$ $R_L = 33 \Omega$ Pulse Duration > 20 μs	I-II-III			25	mA
		IV			50	
V_{GT}	$T_J = 25^\circ\text{C}$ $V_D = 12 \text{ V}$ Pulse Duration > 20 μs	I-II-III-IV			1.5	V
V_{GD}	$T_J = 110^\circ\text{C}$ $V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	I-II-III-IV	0.2			V
I_H^*	$T_J = 25^\circ\text{C}$ $I_T = 100 \text{ mA}$ Gate Open			8		mA
I_L	$T_J = 25^\circ\text{C}$ $V_D = 12 \text{ V}$ $I_G = 100 \text{ mA}$ Pulse Duration > 20 μs	I-II-III-IV		8		mA
V_{TM}^*	$T_J = 25^\circ\text{C}$ $I_{TM} = 1.4 \text{ A}$ $t_p = 10 \text{ ms}$				1.8	V
I_{DRM}^*	V_{DRM} Specified	$T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$			0.01	mA
					0.75	
dv/dt^*	$T_J = 110^\circ\text{C}$ Gate Open Linear Slope up to $V_D = 67\% V_{DRM}$		20			V/ μs
$(dv/dt)_c^*$	$T_J = 40^\circ\text{C}$ $V_D = V_{DRM}$ $(di/dt)_c = 0.4 \text{ A/ms}$		5			V/ μs
t_{gt}	$T_J = 25^\circ\text{C}$ $V_D = V_{DRM}$ $I_G = 100 \text{ mA}$ $di_G/dt = 1 \text{ A}/\mu\text{s}$	I-II-III-IV		3		μs

* For either polarity of electrode A₂ voltage with reference to electrode A₁.

PACKAGE MECHANICAL DATA

TL Plastic



Cooling method : by convection (method A)

Marking : type number

Weight : 0.8 g.

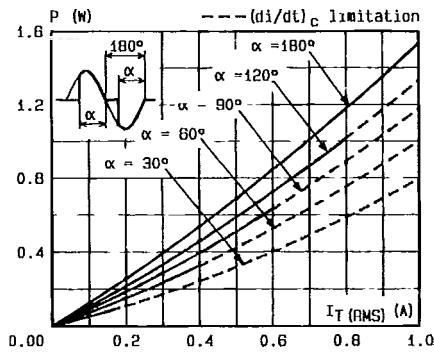


Fig.1 - Maximum mean power dissipation versus RMS on-state current.

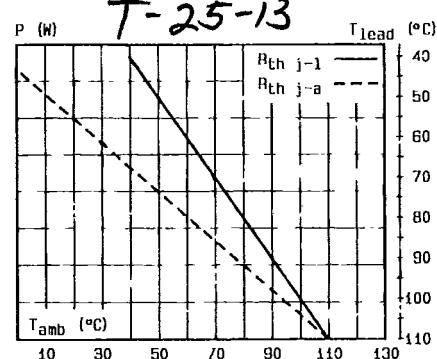


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{lead}).

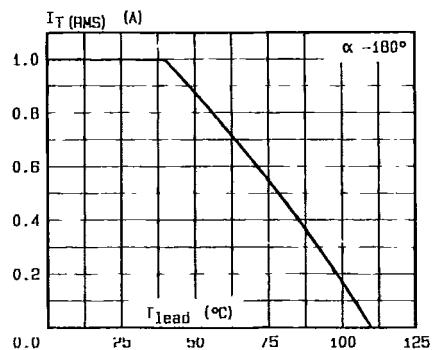


Fig.3 - RMS on-state current versus lead temperature.

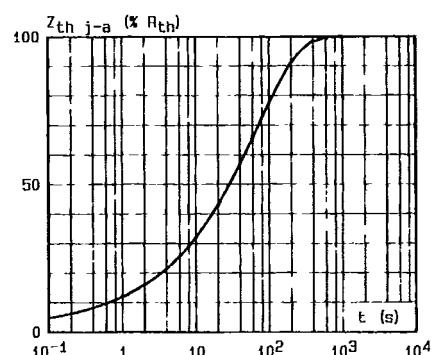


Fig.4 - Thermal transient impedance junction to ambient versus pulse duration.

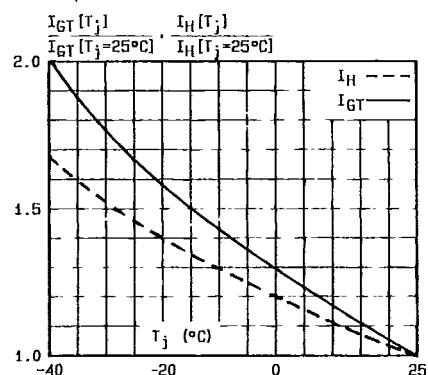


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

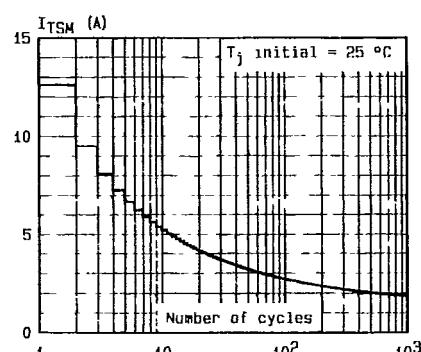


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

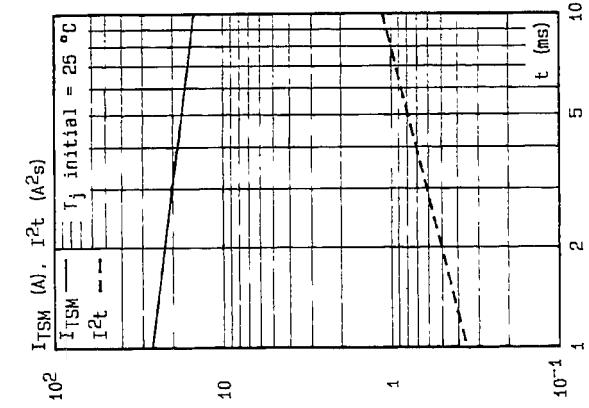


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10$ ms, and corresponding value of I_{2t} .

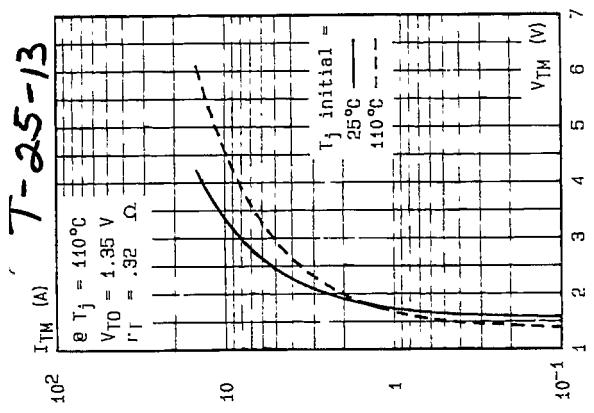


Fig.8 - On-state characteristics
(maximum values).